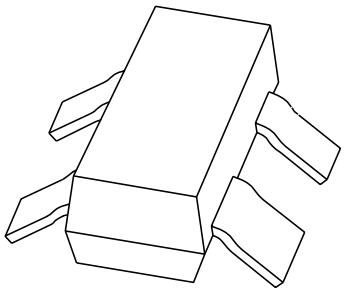
DATA SHEET



BFG590; BFG590/X
NPN 5 GHz wideband transistors

Product specification
Supersedes data of 1995 Sep 19

1998 Oct 02

Philips
Semiconductors

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NPN 5 GHz wideband transistors BFG590; BFG590/X

FEATURES

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability.

APPLICATIONS

- MATV/CATV amplifiers and RF communications subscriber equipment in the GHz range
- Ideally suitable for use in class-A, (A)B and C amplifiers with either pulsed or continuous drive.

DESCRIPTION

NPN silicon planar epitaxial transistor in a 4-pin dual-emitter SOT143B plastic package.

MARKING

TYPE NUMBER	CODE
BFG590	N38
BFG590/X	N44

PINNING

PIN	DESCRIPTION	
	BFG590	BFG590/X
1	collector	collector
2	base	emitter
3	emitter	base
4	emitter	emitter

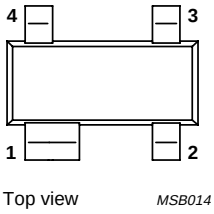


Fig.1 Simplified outline SOT143B.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	–	15	V
I_C	collector current (DC)		–	–	200	mA
P_{tot}	total power dissipation	$T_s \leq 60$ °C	–	–	400	mW
h_{FE}	DC current gain	I_C = 35 mA; V_{CE} = 8 V	50	90	280	
C_{re}	feedback capacitance	I_C = 0; V_{CE} = 8 V; f = 1 MHz	–	0.7	–	pF
f_T	transition frequency	I_C = 80 mA; V_{CE} = 4 V; f = 1 GHz	–	5	–	GHz
G_{UM}	maximum unilateral power gain	I_C = 80 mA; V_{CE} = 4 V; f = 900 MHz; T_{amb} = 25 °C	–	13	–	dB
$\|S_{21}\|^2$	insertion power gain	I_C = 80 mA; V_{CE} = 4 V; f = 900 MHz; T_{amb} = 25 °C	–	11	–	dB

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	15	V
V_{EBO}	emitter-base voltage	open collector	–	3	V
I_C	collector current (DC)		–	200	mA
P_{tot}	total power dissipation	$T_s \leq 60$ °C; see Fig.2; note 1	–	400	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	175	°C

Note

1. T_s is the temperature at the soldering point of the collector pin.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point	$T_s \leq 60$ °C; note 1	290	K/W

Note

1. T_s is the temperature at the soldering point of the collector pin.

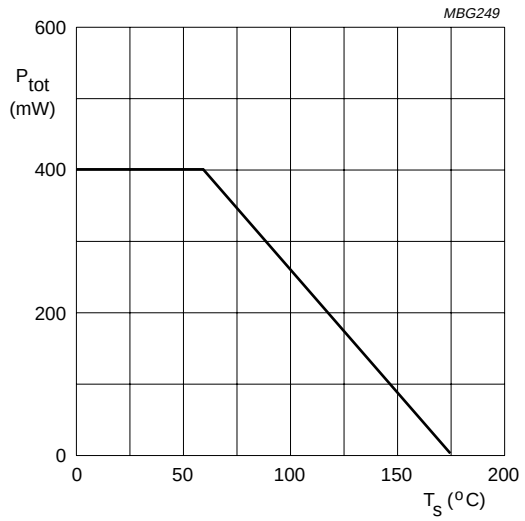


Fig.2 Power derating curve.

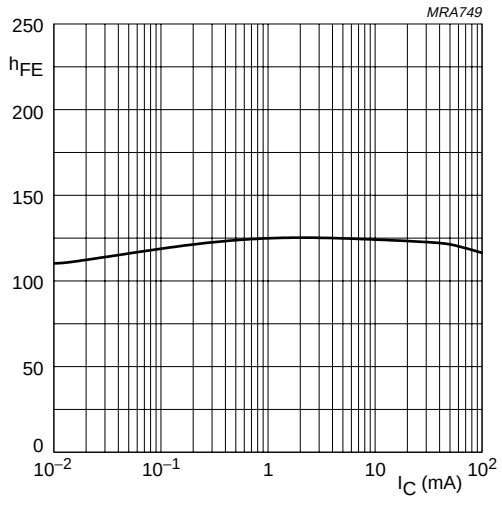
CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	I_C = 0.1 mA; I_E = 0	20	–	–	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	I_C = 10 mA; I_B = 0	15	–	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	I_E = 0.1 mA; I_C = 0	3	–	–	V
I_{CBO}	collector-base leakage current	V_{CB} = 10 V; I_E = 0	–	–	100	nA
h_{FE}	DC current gain	I_C = 70 mA; V_{CE} = 8 V; see Fig.3	60	120	250	
f_T	transition frequency	I_C = 80 mA; V_{CE} = 4 V; f = 1 GHz; see Fig.5	–	5	–	GHz
C_{re}	feedback capacitance	I_C = 0; V_{CB} = 8 V; f = 1 MHz; see Fig.4	–	0.7	–	pF
G_{UM}	maximum unilateral power gain; note 1	I_C = 80 mA; V_{CE} = 4 V; f = 900 MHz; T_{amb} = 25 °C	–	13	–	dB
		I_C = 80 mA; V_{CE} = 4 V; f = 2 GHz; T_{amb} = 25 °C	–	7.5	–	dB
$\|S_{21}\|^2$	insertion power gain	I_C = 80 mA; V_{CE} = 4 V; f = 900 MHz; T_{amb} = 25 °C	–	11	–	dB

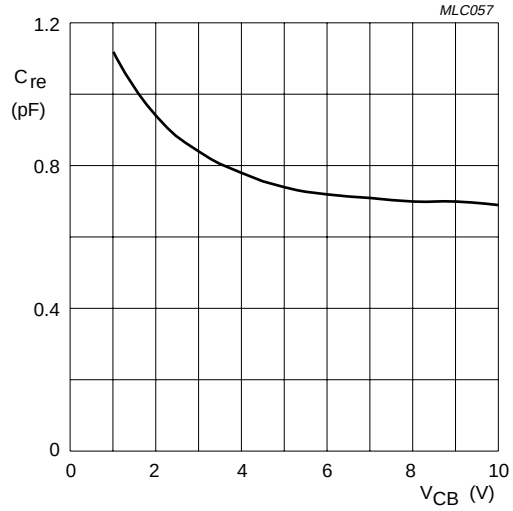
Note

1. G_{UM} is the maximum unilateral power gain, assuming S_{12} is zero and $G_{UM} = 10 \log \frac{|S_{21}|^2}{(1-|S_{11}|^2)(1-|S_{22}|^2)}$ dB.



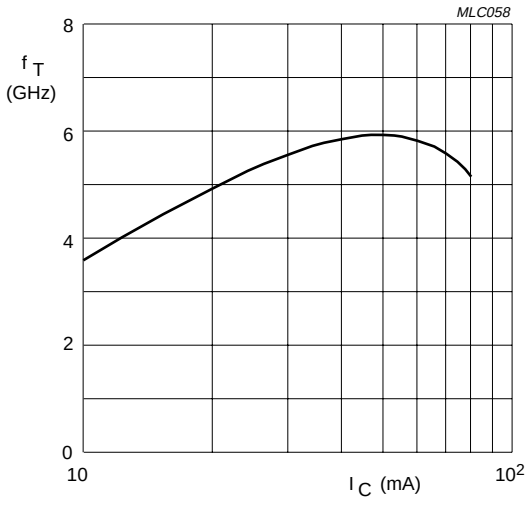
V_{CE} = 8 V.

Fig.3 DC current gain as a function of collector current; typical values.



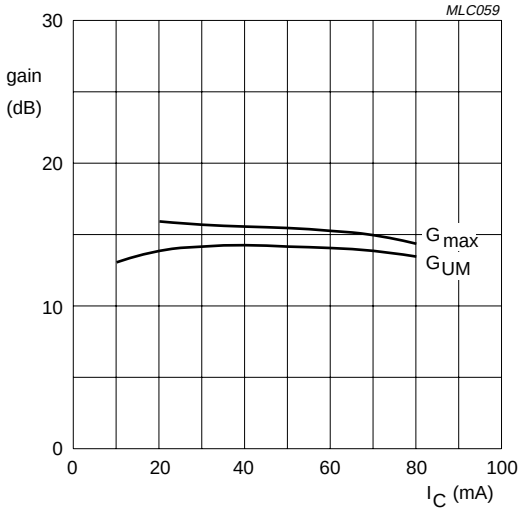
I_C = 0; f = 1 MHz.

Fig.4 Feedback capacitance as a function of collector-base voltage; typical values.



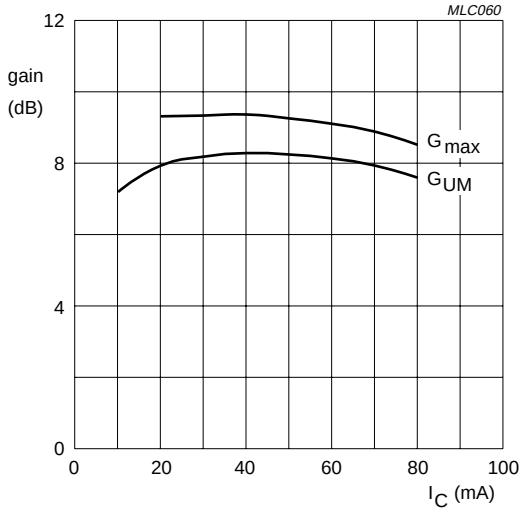
V_{CE} = 4 V; f = 1 GHz.

Fig.5 Transition frequency as a function of collector current; typical values.



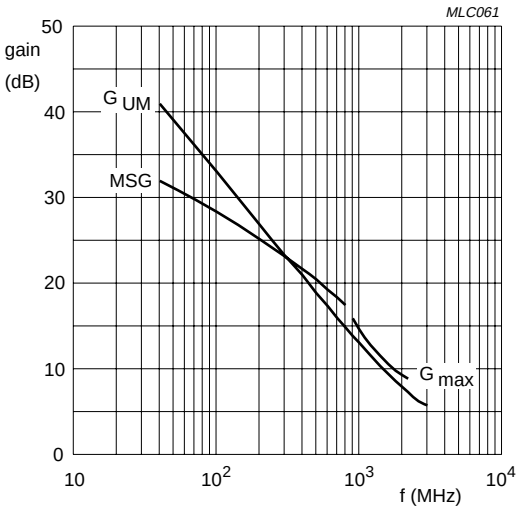
f = 900 MHz; V_{CE} = 4 V.

Fig.6 Gain as a function of collector current; typical values.



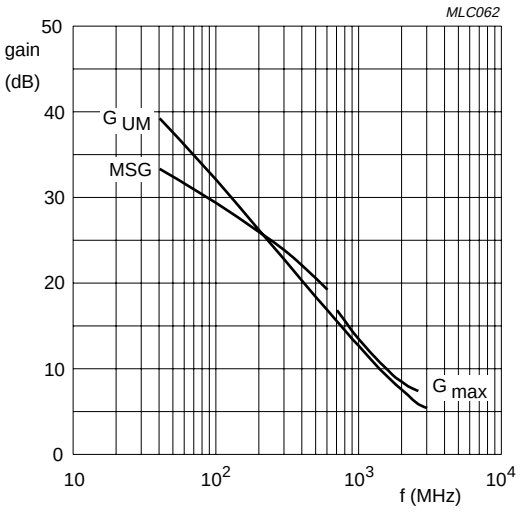
f = 2 GHz; V_{CE} = 4 V.

Fig.7 Gain as a function of collector current; typical values.



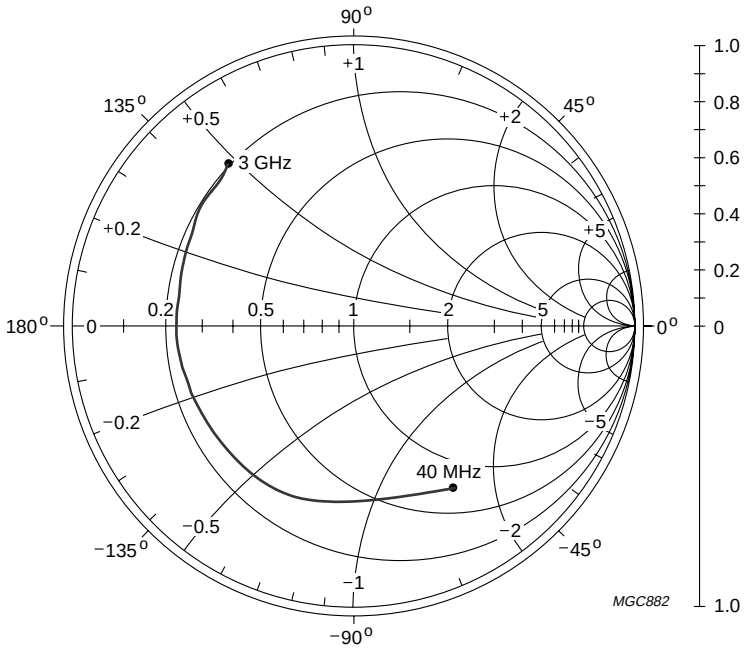
I_C = 20 mA; V_{CE} = 4 V.

Fig.8 Gain as a function of frequency; typical values.



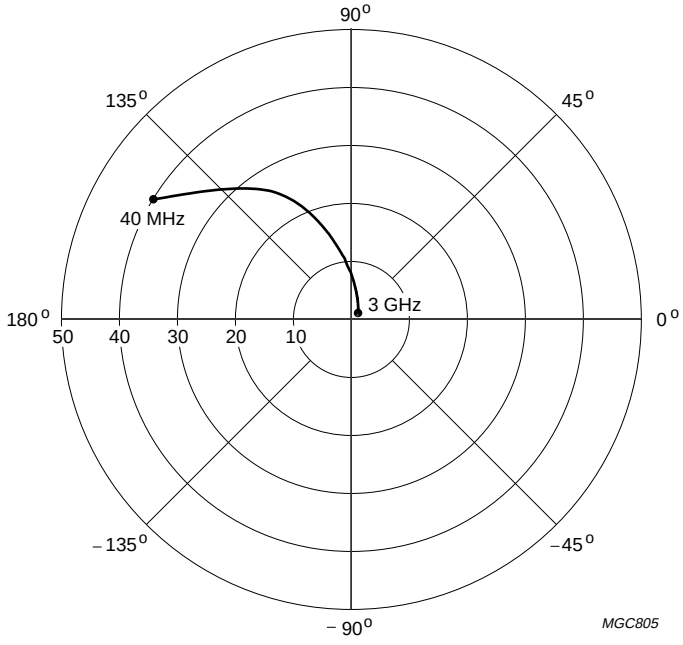
I_C = 80 mA; V_{CE} = 4 V.

Fig.9 Gain as a function of frequency; typical values.



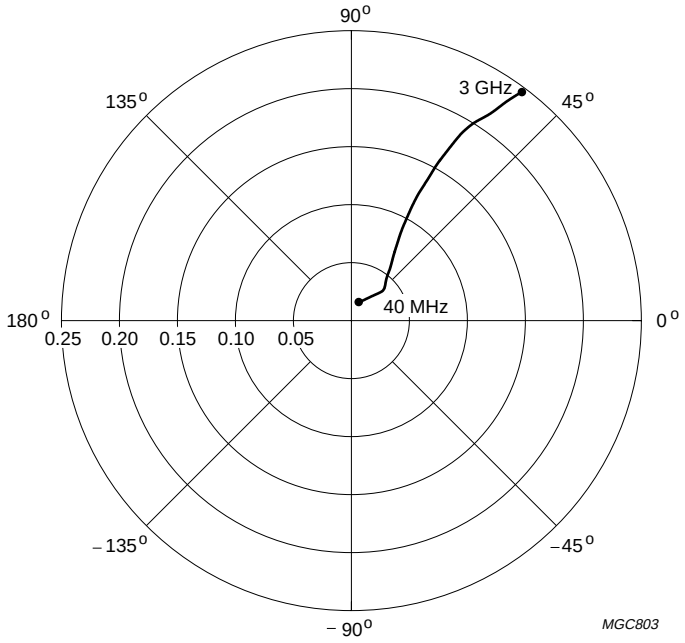
I_C = 80 mA; V_{CE} = 4 V; Z_o = 50 Ω.

Fig.10 Common emitter input reflection coefficient (S_{11}); typical values.



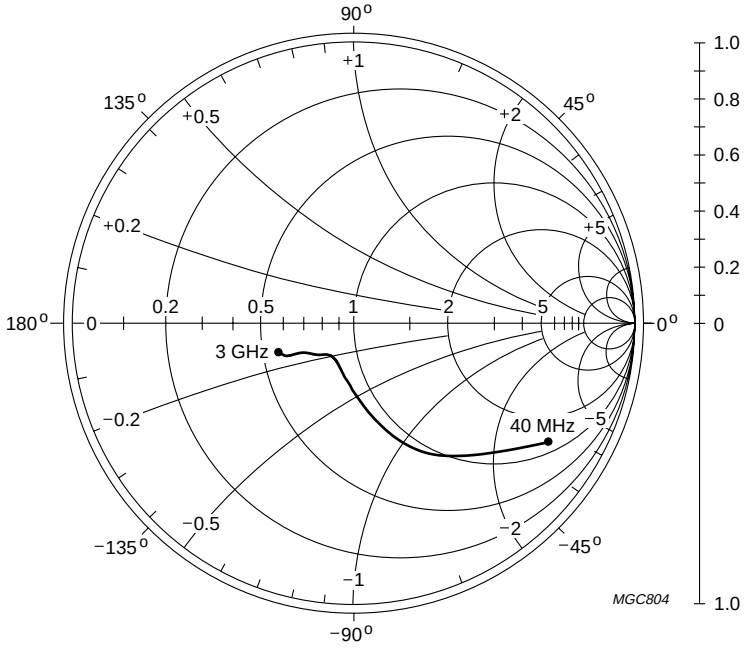
I_C = 80 mA; V_{CE} = 4 V.

Fig.11 Common emitter forward transmission coefficient (S_{21}); typical values.



I_C = 80 mA; V_{CE} = 4 V.

Fig.12 Common emitter reverse transmission coefficient (S_{12}); typical values.

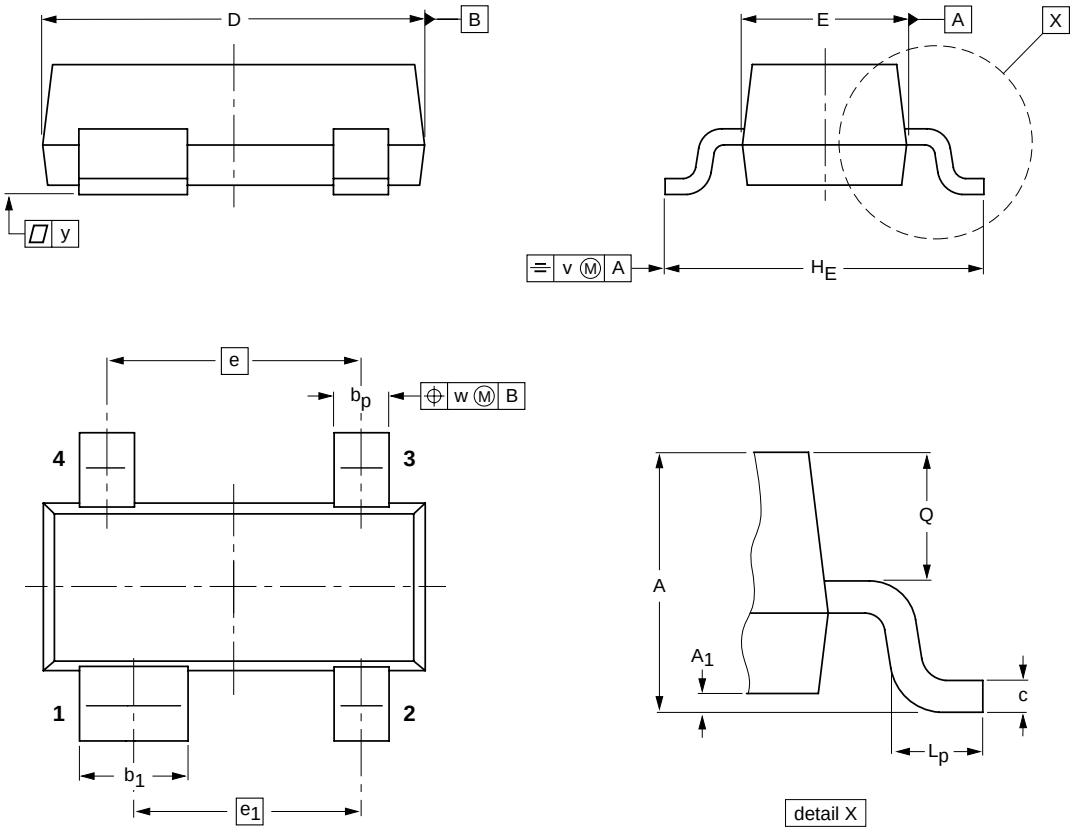


I_C = 80 mA; V_{CE} = 4 V; Z_o = 50 Ω.

Fig.13 Common emitter output reflection coefficient (S_{22}); typical values.

PACKAGE OUTLINE

Plastic surface mounted package; 4 leads **SOT143B**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	b_1	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.9	0.1	0.48 0.38	0.88 0.78	0.15 0.09	3.0 2.8	1.4 1.2	1.9	1.7	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT143B						97-02-28

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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